



09/747,848

AMENDMENT IN RESPONSE TO
(OFFICE ACTION DATED DECEMBER 12, 2002)

#18/C
3-31-03
PATENT
Mueish

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Vladislav Vashchenko et al.

Appln. No.: 09/747,848 ✓

Filed: December 21, 2000 ✓

For: DIODE JUNCTION BASED
ELECTROSTATIC DISCHARGE (ESD)
PROTECTION STRUCTURE

Group Art Unit: 2811

Examiner: O. Nadav

AMENDMENT (IN RESPONSE TO OFFICE
ACTION DATED DECEMBER 12, 2002)

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the
United States Postal Service, postage prepaid, in an envelope,
addressed to Box Non-Fee Amd., Commissioner for Patents,
Washington D.C. 20231-9999 on March 13, 2003.

Commissioner for Patents
Washington, D.C. 20231

Dated: 03-12-03

By: [Signature]

Dear Sir:

In response to the Official Action mailed December 12, 2002, please amend the
above-identified application as follows:

In the Claims

✓ Claims 1-10 and 12-15 have been cancelled. (Claim 11 was previously cancelled.)

The claims have been amended to read as follows:

16. (Amended) The structure of claim 17 wherein the semiconductor material
has a dopant concentration that is less than the dopant concentration of the second region.

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17. (Amended) An ESD protection structure formed in a semiconductor
material of a first conductivity type, the structure comprising:
an isolation region formed in the semiconductor material;
a first region of a second conductivity type formed in the semiconductor material, the
first region having a dopant concentration;

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